

# PRODUCT RELIABILITY REPORT FOR

**DS1123L**, Rev A5

# **Maxim Integrated Products**

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## Prepared by:

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#### Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Maxim products:

In addition, Maxim's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

### **Device Description:**

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l\_datasheet3.cfm.

#### **Reliability Derating:**

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

```
AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts
AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10-5 eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)
```

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

```
AfV = exp(B*(Vs - Vu))

AfV = Acceleration factor due to Voltage

Vs = Stress Voltage (e.g. 7.0 volts)

Vu = Maximum Operating Voltage (e.g. 5.5 volts)

B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)
```

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

```
Fr = X/(ts * AfV * AfT * N * 2)
X = Chi-Sq statistical upper limit
N = Life test sample size
```

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: MTTF (YRS): 81361 FITS: 1.4

DEVICE HOURS: 692416 FAILS: 0

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 B: 0 Tu: 25 °C Vu: 5.5 Volts

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. "\*" after DATE CODE denotes specific product data and SEQ No. to identify specific line items in the report for comments when required.

#### **Device Information:**

Process: E6W-2P2M,HPVt,E2,EPROGVt,TCZ ALOCOS:GOI 5" Reticles

Passivation: Passivation w/Nov TEOS Oxide-Nitride

Die Size: 81 x 80

Number of Transistors: 1

Interconnect: Aluminum / 0.5% Copper

Gate Oxide Thickness: 150 Å

DESCRIPTION	DATE CODE/SEQ CONDITION			REA	ADPOINT	QTY	FAILS	FA#
ESD SENSITIVITY	0439		EOS/ESD S5.1 HBM 500 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0439		EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0439		EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0439		EOS/ESD S5.1 HBM 4000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0439		EOS/ESD S5.1 HBM 8000 VOLTS	1	PUL'S	3	3	No FA
LATCH-UP	0439		JESD78, I-TEST 125C			6	0	
LATCH-UP	0439		JESD78, V-SUPPLY TEST 125C			6	0	
ESD SENSITIVITY	0636	* 1	EOS/ESD S5.1 HBM 500 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0636	* 2	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0636	* 3	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0636	* 4	EOS/ESD S5.1 HBM 4000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0636	* 5	EOS/ESD S5.1 HBM 8000 VOLTS	1	PUL'S	3	3	No FA
LATCH-UP	0636	* 6	JESD78, I-TEST 125C			6	0	
LATCH-UP	0636	* 7	JESD78, V-SUPPLY TEST 125C			6	0	
					Total:		6	

OPERATING LIFE											
DESCRIPTION	DATE CODE/SEQ CONDITION					REA	DPOINT	QTY	FAILS	FA#	
HIGH TEMP OP LIFE	0506		125C, 5.5 \	/OLTS		1000	HRS	77	0		
HIGH TEMP OP LIFE	0507		125C, 5.5 \	/OLTS		1000	HRS	77	0		
HIGH TEMP OP LIFE	0507		125C, 5.5 \	/OLTS		1000	HRS	77	0		
HIGH TEMP OP LIFE	0507		125C, 5.25	VOLTS		408	HRS	77	0		
HIGH TEMP OP LIFE	0525		125C, 5.5 \	/OLTS		1000	HRS	77	0		
HIGH TEMP OP LIFE	0526		125C, 5.5 \	/OLTS		1000	HRS	77	0		
HIGH TEMP OP LIFE	0527		125C, 5.5 \	/OLTS		1000	HRS	77	0		
HIGH TEMP OP LIFE	0536		125C, 3.6 V	/OLTS		1000	HRS	77	0		
HIGH TEMP OP LIFE	0607		125C, 5.5 \	/OLTS		1000	HRS	77	0		
HIGH TEMP OP LIFE	0636	* 4	125C, 3.6 V	125C, 3.6 VOLTS		1000 HRS			45 0		
						Total:			0		
W/E ENDURANCE	AND DA	TA RE	T'N								
DESCRIPTION	DATE CODE/SEQ CONDITION					REA	DPOINT	QTY	FAILS	FA#	
WRITE CYCLE STRESS (KCYS)	0507		70 C, 5.25	VOLTS		5	KCYS	77	0		
STORAGE LIFE			150C			500	HRS	77	0		
							Total:		0		
FAILURE RATE:	MTTF (YRS): 81361 FITS:						1.4				
	DEVICE HOURS: 692416				FAILS:		0				